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STPS3060CW

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I _{F(AV)}	2 x 15 A	
V _{RRM}	60 V	
Tj (max)	150°C	
V _F (max)	0.75 V	

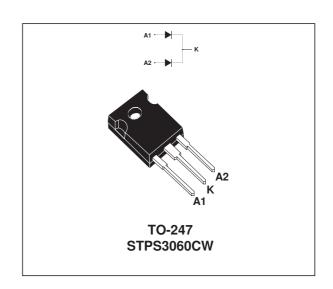
FEATURES AND BENEFITS

- Negligible switching losses
- Low forward voltage drop
- Low capacitance
- High reverse avalanche surge capability.



High voltage dual Schottky rectifier suited for switchmode power supplies and other power converters.

Packaged in TO-247, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses and low noise are required.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage	60	V		
I _{F(RMS)}	RMS forward current	30	Α		
I _{F(AV)}	9		Per diode Per device	15 30	А
I _{FSM}	Surge non repetitive forward current	tp = 10 ms Sinusoidal	Per diode	200	А
I _{RRM}	Repetitive peak reverse current	tp=2 μs F=1kHz	Per diode	1	Α
I _{RSM}	Non repetitive peak reverse current	1	Α		
T _{stg}	Storage temperature range	- 65 to + 150	°C		
Tj	Maximum operating junction temperatu	150	°C		
dV/dt	Critical rate of rise of reverse voltage	1000	V/µs		

^{* :} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ thermal runaway condition for a diode on its own heatsink

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	Per diode Total	1.5 0.8	°C/W
R _{th(c)}		Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously : Δ Tj(diode 1) = P(diode1) x R_{th(j-c)}(Per diode) + P(diode 2) x R_{th(c)}

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Co	Min.	Тур.	Max.	Unit	
I _R *	Reverse leakage	Tj = 25°C	$V_R = V_{RRM}$			150	μΑ
	current	Tj = 125°C				100	mA
V _F *	Forward voltage drop	Tj = 25°C	I _F = 15 A			0.85	V
		Tj = 125°C	I _F = 15 A		0.65	0.75	
		Tj = 25°C	I _F = 30 A			1.05	
		Tj = 125°C	I _F = 30 A		0.80	0.90	

Pulse test: * tp = 5ms, δ < 2%

To evaluate the maximum conduction losses use the following equation:

 $P = 0.6 \times I_{F(AV)} + 0.01 I_{F}^{2}_{(RMS)}$

Fig. 1: Conduction losses versus average current (per diode).

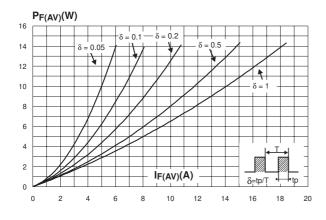
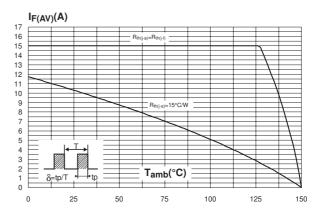


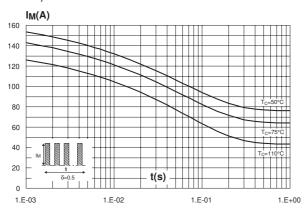
Fig. 2: Average forward current versus ambient temperature (δ =0.5, per diode).



2/4

^{**}tp = 380 μ s, δ < 2%

Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).



junction to case versus pulse duration.

Fig. 4: Relative variation of thermal impedance

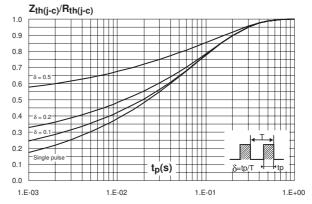


Fig. 5: Reverse leakage currrent versus reverse voltage applied (typical values, per diode).

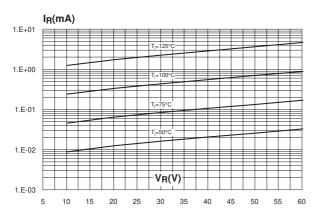


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).

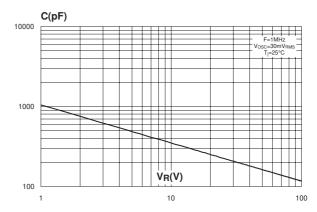
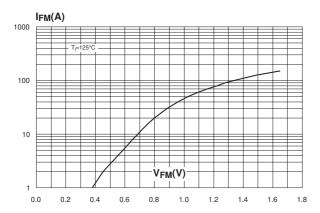


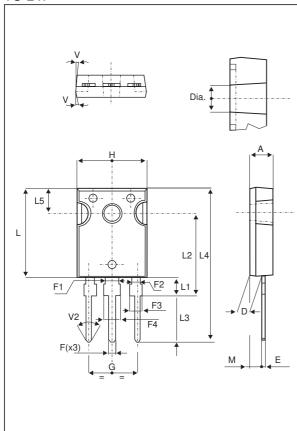
Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).



3/4

PACKAGE MECHANICAL DATA

TO-247



DIMENSIONS							
REF.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.85		5.15	0.191		0.203	
D	2.20		2.60	0.086		0.102	
Е	0.40		0.80	0.015		0.031	
F	1.00		1.40	0.039		0.055	
F1		3.00			0.118		
F2		2.00			0.078		
F3	2.00		2.40	0.078		0.094	
F4	3.00		3.40	0.118		0.133	
G		10.90			0.429		
Н	15.45		15.75	0.608		0.620	
L	19.85		20.15	0.781		0.793	
L1	3.70		4.30	0.145		0.169	
L2		18.50			0.728		
L3	14.20		14.80	0.559		0.582	
L4		34.60			1.362		
L5		5.50			0.216		
М	2.00		3.00	0.078		0.118	
V		5°			5°		
V2		60°			60°		
Dia.	3.55		3.65	0.139		0.143	

■ Cooling method : C

Recommended torque value : 0.8m.NMaximum torque value : 1.0m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS3060CW	STPS3060CW	TO-247	4.4 g	50	Tube

■ Epoxy meets UL94,V0

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